

# Bridge Rectifier

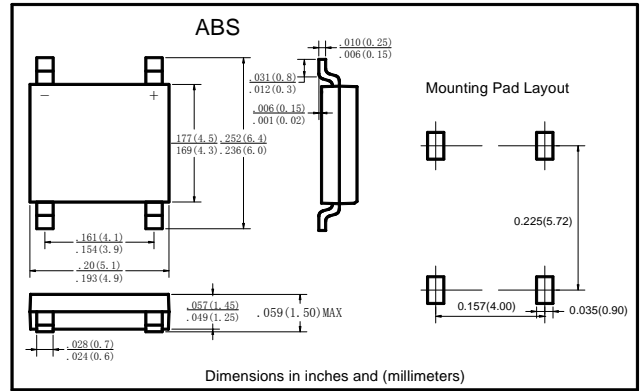
## ■ Features

- $I_o$  1A
- $V_{RRM}$  200V~1000V
- Glass passivated chip
- High surge forward current capability

## ■ Applications

- General purpose 1 phase Bridge rectifier applications

## ■ Outline Dimensions and Mark



## ■ Limiting Values (Absolute Maximum Rating)

Item	Symbol	Unit	Conditions	ABS				
				2	4	6	8	10
Repetitive Peak Reverse Voltage	$V_{RRM}$	V		200	400	600	800	1000
Average Rectified Output Current	$I_o$	A	60Hz sine wave, R-load, $T_a=25^\circ\text{C}$	On alumina substrate		1.0		
Surge(Non-repetitive)Forward Current	$I_{FSM}$	A	60Hz sine wave, 1 cycle, $T_j=25^\circ\text{C}$	30				
Current Squared Time	$I^2t$	$\text{A}^2\text{S}$	$1\text{ms} \leq t < 8.3\text{ms}$ $T_j=25^\circ\text{C}$ , Rating of per diode	3.7				
Storage Temperature	$T_{stg}$	$^\circ\text{C}$		-55 ~ +150				
Junction Temperature	$T_j$	$^\circ\text{C}$		-55 ~ +150				

## ■ Electrical Characteristics ( $T_a=25^\circ\text{C}$ Unless otherwise specified)

Item	Symbol	Unit	Test Condition	Max
Peak Forward Voltage	$V_{FM}$	V	$I_{FM}=0.4\text{A}$ , Pulse measurement, Rating of per diode	0.95
Peak Reverse Current	$I_{RRM}$	$\mu\text{A}$	$V_{RM}=V_{RRM}$ , Pulse measurement, Rating of per diode	10
热阻 Thermal Resistance	$R_{\theta J-A}$	$^\circ\text{C}/\text{W}$	Between junction and ambient, On alumina substrate	62.5
	$R_{\theta J-L}$		Between junction and lead	25



# ABS2 ~ ABS10

## RATINGS AND CHARACTERISTIC CURVES

( $T_A=25^\circ\text{C}$  unless otherwise noted)

FIG1:  $I_o$ - $T_a$  Curve

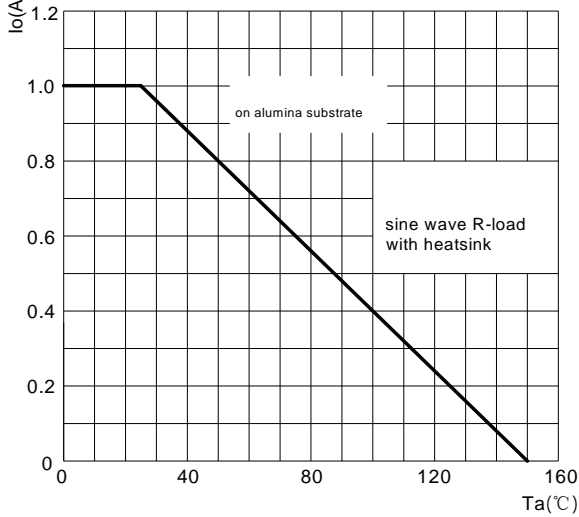


FIG2: Surge Forward Current Capability

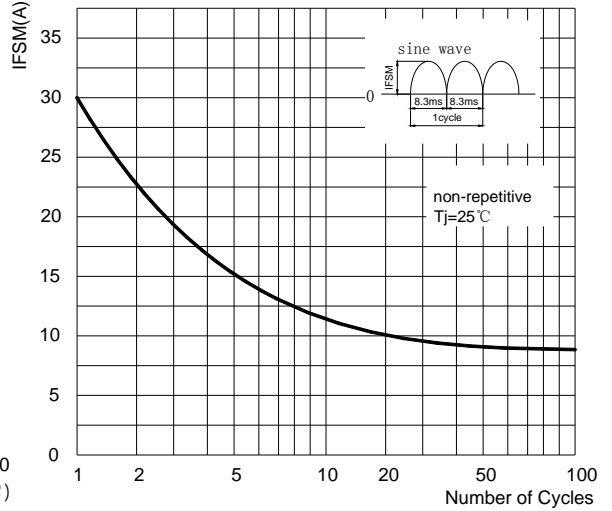


FIG3: Forward Voltage

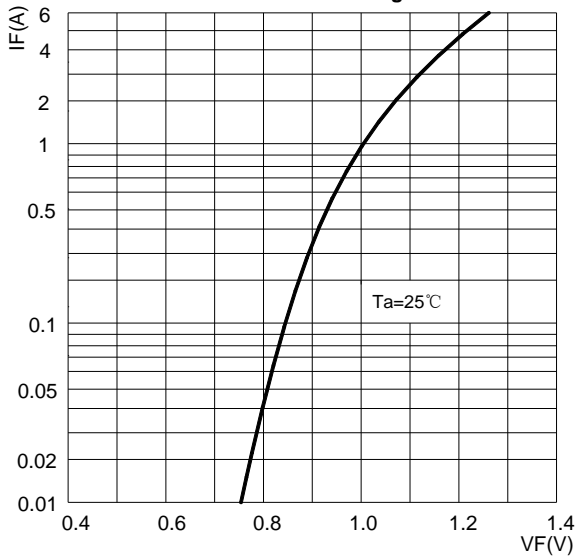


FIG4: Typical Reverse Characteristics

